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chambers has a vacuum pressure generator for forming vacuum pressure therein.

8. (Amended) The multi-chamber system of an etching facility for manufacturing semiconductor devices according to claim 1, wherein the plurality of processing chambers have one common load lock chamber:

Three Times

20. (~~Twice~~[^] Amended) A multi-chamber system of an etching facility for manufacturing semiconductor devices comprising:

a cassette stage for mounting a cassette having wafers stacked thereon;

a transfer path adjacent to the cassette stage for providing space for transportation of wafers, the transfer path being at atmospheric pressure and having a width slightly larger than a diameter of the wafers;

a plurality of processing chambers aligned in a plurality of layers parallel to and beside the transfer path; *[and]*

a transfer mechanism capable of vertical/horizontal reciprocal movement installed in the transfer path for loading and unloading the wafers stacked on the cassette stage.

; and IP a load lock chamber connected to one side of the processing chambers, the load lock chamber serving as a stand-by area for the wafers

31. (Twice Amended) A multi-chamber system of an etching facility for manufacturing semiconductor devices comprising:

a first cassette stage for mounting a cassette having unprocessed wafers

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a transfer mechanism capable of vertical/horizontal reciprocal movement installed in the transfer path for loading and unloading the wafers stacked on the cassette stage to the plurality of processing chambers.

22. (Amended) The multi-chamber system of an etching facility for manufacturing semiconductor devices according to claim 20, wherein the plurality of layers [multi-layers] of the processing chambers include [number] 2 to 5 layers.

24. ^{Twice} (Amended) The multi-chamber system of an etching facility for manufacturing semiconductor devices according to claim ²⁰ 23, wherein the load lock chamber comprises:

a transfer arm for receiving wafers from the transfer mechanism and transferring the wafers to the processing [chamber] chambers;

an inner transfer device for moving the transfer arm; and

gates formed on a side of the transfer path and [a side] sides of the processing chambers [chamber], respectively, the gates being selectively opened and closed to allow passage of the wafers.

26. (Amended) The multi-chamber system of an etching facility for manufacturing semiconductor devices according to claim 20, wherein the transfer mechanism comprises: